

Customer No.: 31561
Application No.: 10/707,110
Docket No.: 12041-US-PA

REMARKS

Present Status of the Application

Claims 1-17 remain pending of which claim 13 has been amended to more explicitly describe the claimed invention in this regard. Amendments to claim 13 is fully supported at paragraph [0013] where it is described that the lightly doped drain region is only formed within the switch thin film transistor. Therefore, it is believed that no new matter adds by way of amendments to claims or otherwise to the application in this regard.

In the outstanding Office Action, claims 1-17 were rejected under 35 U.S.C. 102(e) as being anticipated by Noguchi et al. (US-6,762,564, hereinafter Noguchi).

For at least the following reasons, Applicant respectfully submits that claims 1-17 are in proper condition for allowance. Reconsideration is respectfully requested.

Discussion of the claim rejection under 35 USC 103

The Office Action rejected claims 1-17 under 35 U.S.C. 102(e) as being anticipated by Noguchi et al. (US-6,762,564, hereinafter Noguchi).

Applicants respectfully disagree and would like to point out that it is well established that rejections under 35 U.S.C. 102 requires that each and every elements of the rejected claims must disclosed exactly by a single prior art reference.

The present invention is directed to a pixel structure of an OLED. The proposed independent claim 1, among other things, recites at least [*....wherein the second gate terminal is coupled to the organic light emitting diode and the first lightly doped drain region and the second lightly doped drain region have different doped concentrations*].

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The advantage of above feature is that at least the luminescence of the light emitting diode may be effectively stabilized.

Applicants respectfully submit that the proposed independent claim 1 is allowable over Noguchi because Noguchi substantially fail to teach, suggest or disclose every features of the claimed invention. More specifically, Noguchi substantially fails to teach, suggest or disclose a pixel structure of an OLED comprising at least [...*wherein the first lightly doped drain region and the second lightly doped drain region have different doped concentrations*] as required by the proposed independent claim 1.

Instead, Noguchi substantially teaches, at FIG. 3a, col. 5, lines 24-32, ions are implanted into the active layers 14a and 14b using the resists as masks, wherein parts of the active layers 14a and 14b not covered with the resists are highly doped with the impurity ions, to be source areas and drain areas, and parts of the active layers 14a and 14b covered with the resists are low doped with the impurity ions, to be LDD areas. However, there is no disclosure on either the concentration profiles of the LLDs, or the structural configuration (lengths or widths) of the LLDs. Accordingly, since Noguchi is completely silent regarding the concentration profiles of the LLDs or the structural configurations (lengths or widths) of the LLDs, and therefore Noguchi cannot possibly anticipate claim 1 in this regard. In other words, Noguchi substantially fails to teach or disclose a pixel structure of an OLED comprising at least [...*wherein the first lightly doped drain region and the second lightly doped drain region have different doped concentrations*] as required by the proposed independent claim 1.

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Furthermore, Applicants respectfully submit that claim 2, which depends from claim 1, further specifies that the doped concentration of the second lightly doped drain region is higher than that of the first lightly doped drain region, and thereby further distinguish from Noguchi.

Because the proposed independent claim 7, among other things recites at least [*the first lightly doped drain region and the second lightly doped drain region have different lengths*], therefore Applicants respectfully submit that claim 7 also patently defines over Noguchi for at least the same reasons discussed above.

Furthermore, Applicants respectfully submit that claim 8, which depends from claim 1, further specifies that the first lightly doped drain region is longer than that of the second lightly doped drain region, and thereby further distinguish from Noguchi.

Furthermore, Noguchi substantially teaches that LLDs are formed in both switch and control thin film transistors. Because the amended proposed independent claim 13, among other things, recites at least [*...no lightly doped drain region is formed in the control thin film transistor*], therefore Applicants respectfully submit that claim 13 also patently defines over Noguchi for at least the same reasons discussed above

Claims 3-6, 9-12 and 14-17, which directly or indirectly depend from independent Claims 1, 7 and 13, respectively, are also patentable over Noguchi at least because of their dependency from an allowable base claim.

For at least the foregoing reasons, Applicant respectfully submits that claims 1-17 patently define over Noguchi. Reconsideration and withdrawal of above rejections is respectfully requested.

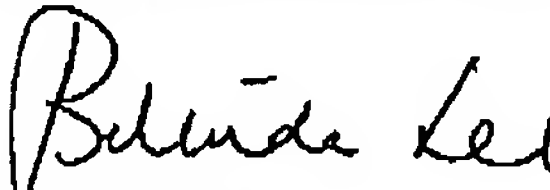
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CONCLUSION

For at least the foregoing reasons, it is believed that all pending claims 1-17 are in proper condition for allowance. If the Examiner believes that a conference would be of value in expediting the prosecution of this application, he is cordially invited to telephone the undersigned counsel to arrange for such a conference.

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Respectfully submitted,


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